# **SM73307**

# **Dual Precision, 17 MHz, Low Noise, CMOS Input Amplifier**

# **General Description**

The SM73307 is a dual, low noise, low offset, CMOS input, rail-to-rail output precision amplifier with a high gain bandwidth product. The SM73307 is ideal for a variety of instrumentation applications including solar photovoltaic.

Utilizing a CMOS input stage, the SM73307 achieves an input bias  $\underline{cu}_T$ rent of 100 fA, an input referred voltage noise of 5.8 nV/ $\!\!\!\!/ Hz$ , and an input offset voltage of less than ±150  $\mu V$ . These features make the SM73307 a superior choice for precision applications.

Consuming only 1.30 mA of supply current per channel, the SM73307 offers a high gain bandwidth product of 17 MHz, enabling accurate amplification at high closed loop gains.

The SM73307 has a supply voltage range of 1.8V to 5.5V, which makes it an ideal choice for portable low power applications with low supply voltage requirements.

The SM73307 is built with National's advanced VIP50 process technology and is offered in an 8-pin MSOP package.

The SM73307 incorporates enhanced manufacturing and support processes for the photovoltaic and automotive market, including defect detection methodologies. Reliability qualification is compliant with the requirements and temperature grades defined in the Renewable Energy Grade and AEC-Q100 standards.

### **Features**

Unless otherwise noted, typical values at  $V_S = 5V$ .

- Renewable Energy Grade
- Input offset voltage ±150 μV (max)
  Input bias current 100 fA
- Input voltage noise 5.8 nV/√Hz
- Input voltage noise 5.8 nV/√Hz
   Gain bandwidth product 17 MHz
- Supply current 1.30 mA
   Supply voltage range 1.8V to 5.5V
- THD+N @ f = 1 kHz 0.001%
- Operating temperature range -40°C to 125°C
- Rail-to-rail output swing
- 8-Pin MSOP package

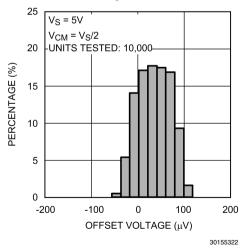
# **Applications**

- Photovoltaic Electronics
- Active filters and buffers
- Sensor interface applications
- Transimpedance amplifiers
- Automotive

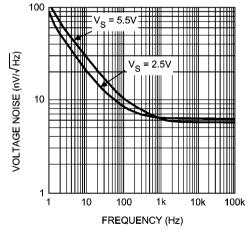


# **Typical Performance**

#### Offset Voltage Distribution



#### Input Referred Voltage Noise



# **Absolute Maximum Ratings** (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

ESD Tolerance (Note 2) Human Body Model 2000V Machine Model 200V 1000V Charge-Device Model V<sub>IN</sub> Differential ±0.3V Supply Voltage  $(V_S = V^+ - V^-)$ 6.0V Voltage on Input/Output Pins  $V^{+} +0.3V, V^{-} -0.3V$ Storage Temperature Range -65°C to 150°C Junction Temperature (Note 3) +150°C Soldering Information
Infrared or Convection (20 sec) 235°C
Wave Soldering Lead Temp. (10 sec) 260°C

# **Operating Ratings** (Note 1)

Temperature Range (*Note 3*)  $-40^{\circ}$ C to 125°C Supply Voltage ( $V_S = V^+ - V^-$ )  $0^{\circ}$ C  $\leq T_A \leq 125^{\circ}$ C 1.8V to 5.5V  $-40^{\circ}$ C  $\leq T_A \leq 125^{\circ}$ C 2.0V to 5.5V

Package Thermal Resistance ( $\theta_{IA}(Note 3)$ )

8-Pin MSOP 236°C/W

## 2.5V Electrical Characteristics

Unless otherwise specified, all limits are guaranteed for  $T_A = 25$ °C,  $V^+ = 2.5$ V,  $V^- = 0$ V , $V_O = V_{CM} = V^+/2$ . **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions		Min (Note 5)	Typ (Note 4)	Max (Note 5)	Units
V <sub>os</sub>	Input Offset Voltage	$-20^{\circ}$ C ≤ T <sub>A</sub> ≤ 85°C $-40^{\circ}$ C ≤ T <sub>A</sub> ≤ 125°C			±20	±180 <b>±330</b>	μV
<b>v</b> os	Imput Offset Voltage				±20	±180 <b>±430</b>	μν
TC V <sub>OS</sub>	Input Offset Voltage Temperature Drift (Note 6, Note 8)				-1.75	±4	μV/°C
I <sub>B</sub>	Input Rice Current	V <sub>CM</sub> = 1.0V	-40°C ≤ T <sub>A</sub> ≤ 85°C		0.05	1 <b>25</b>	pA
	Input Bias Current	(Note 7, Note 8)	-40°C ≤ T <sub>A</sub> ≤ 125°C		0.05	1 <b>100</b>	
I <sub>os</sub>	Input Offset Current	V <sub>CM</sub> = 1V ( <i>Note 8</i> )			0.006	0.5 <b>50</b>	pA
CMRR	Common Mode Rejection Ratio	0V ≤ V <sub>CM</sub> ≤ 1.4V		83 <b>80</b>	100		dB
		$2.0V \le V^{+} \le 5.5V$ V- = 0V, V <sub>CM</sub> = 0		85 <b>80</b>	100		- dB
PSRR	Power Supply Rejection Ratio	$1.8V \le V^{+} \le 5.5V$ $V^{-} = 0V, V_{CM} = 0$		85	98		
CMVR	Common Mode Voltage Range	CMRR ≥ 80 dB CMRR ≥ 78 dB		-0.3 <b>-0.3</b>		1.5 <b>1.5</b>	V
•		$V_{O} = 0.15 \text{ to } 2.2V$ $R_{L} = 2 \text{ k}\Omega \text{ to } V + / 2$ $V_{O} = 0.15 \text{ to } 2.2V$ $R_{L} = 10 \text{ k}\Omega \text{ to } V + / 2$		84 <b>80</b>	92		
A <sub>VOL</sub>	Open Loop Voltage Gain			90 <b>86</b>	95		dB
V <sub>OUT</sub>	Output Voltage Swing High	$R_L = 2 \text{ k}\Omega \text{ to V+/2}$			25	70 <b>77</b>	
		$R_L = 10 \text{ k}\Omega \text{ to V+/2}$			20	60 <b>66</b>	mV from
	Output Voltage Swing Low	$R_L = 2 \text{ k}\Omega \text{ to V+/2}$			30	30 70 eith	
		$R_L = 10 \text{ k}\Omega \text{ to V} + 1/2$	2		15	60 <b>62</b>	

Symbol	Parameter	Conditions	Min ( <i>Note 5</i> )	Typ (Note 4)	Max ( <i>Note 5</i> )	Units	
I <sub>OUT</sub>	Output Current	Sourcing to V- V <sub>IN</sub> = 200 mV ( <i>Note 9</i> )	36 <b>30</b>	52		m A	
		Sinking to V+ V <sub>IN</sub> = -200 mV ( <i>Note 9</i> )	7.5 <b>5.0</b>	15		mA	
I <sub>S</sub>	Supply Current	Per Channel		1.10	1.50 <b>1.85</b>	mA	
SR	Slew Rate	A <sub>V</sub> = +1, Rising (10% to 90%)		8.3		V/µs	
		A <sub>V</sub> = +1, Falling (90% to 10%)		10.3			
GBW	Gain Bandwidth			14		MHz	
e <sub>n</sub>	Input Referred Voltage Noise Density	f = 400 Hz		6.8		nV/√Hz	
		f = 1 kHz		5.8		NV/√ ⊓Z	
i <sub>n</sub>	Input Referred Current Noise Density	f = 1 kHz		0.01		pA/√Hz	
THD+N	Total Harmonic Distortion + Noise	$f = 1 \text{ kHz}, A_V = 1, R_L = 100 \text{ k}Ω$ $V_O = 0.9 V_{PP}$		0.003		%	
		$f = 1 \text{ kHz}, A_V = 1, R_L = 600\Omega$ $V_O = 0.9 V_{PP}$		0.004		-70	

# **5V Electrical Characteristics**

Unless otherwise specified, all limits are guaranteed for  $T_A = 25^{\circ}C$ ,  $V^{+} = 5V$ ,  $V^{-} = 0V$ ,  $V_{CM} = V^{+}/2$ . **Boldface** limits apply at the temperature extremes.

Symbol	Parameter	Conditions		Min (Note 5)	Typ (Note 4)	Max (Note 5)	Units	
V <sub>OS</sub> Input Offset Voltage		-20°C ≤ T <sub>A</sub> ≤ 85°C			±10	±150 ±300	/	
V <sub>os</sub>	Imput Offset Voltage	-40°C ≤ T <sub>A</sub> ≤ 125°C			±10	±150 ±400	μV	
TC V <sub>os</sub>	Input Offset Voltage Temperature Drift (Note 6, Note 8)				-1.75	±4	μV/°C	
	B Input Bias Current	V <sub>CM</sub> = 2.0V ( <i>Note 7, Note 8</i> )	-40°C ≤ T <sub>A</sub> ≤ 85°C		0.1	1 <b>25</b>	pA	
I <sub>B</sub>			-40°C ≤ T <sub>A</sub> ≤ 125°C		0.1	1 100		
I <sub>os</sub>	Input Offset Current	V <sub>CM</sub> = 2.0V ( <i>Note 8</i> )			0.01	0.5 <b>50</b>	pA	
CMRR	Common Mode Rejection Ratio	0V ≤ V <sub>CM</sub> ≤ 3.7V		85 <b>82</b>	100		dB	
PSRR	Power Supply Rejection Ratio	$2.0V \le V^{+} \le 5.5V$ $V^{-} = 0V, V_{CM} = 0$		85 <b>80</b>	100		-ID	
PORK		$1.8V \le V^{+} \le 5.5V$ V <sup>-</sup> = 0V, V <sub>CM</sub> = 0		85	98		dB	
CMVR	Common Mode Voltage Range	CMRR ≥ 80 dB CMRR ≥ 78 dB		-0.3 <b>-0.3</b>		4 <b>4</b>	V	
_	Open Loop Voltage Gain	$V_{O} = 0.3 \text{ to } 4.7V$ $R_{L} = 2 \text{ k}\Omega \text{ to } V^{+}/2$		84 <b>80</b>	90		٦D	
A <sub>VOL</sub>		$V_{O} = 0.3 \text{ to } 4.7 \text{V}$ $R_{L} = 10 \text{ k}\Omega \text{ to } \text{V} + /3$	2	90 <b>86</b>	95		dB	

Symbol	Parameter	Conditions	Min (Note 5)	Typ (Note 4)	Max (Note 5)	Units	
V <sub>OUT</sub>	Output Voltage Swing High	$R_L = 2 \text{ k}\Omega \text{ to V+/2}$		32	70 <b>77</b>		
		$R_L = 10 \text{ k}\Omega \text{ to V+/2}$		22	60 <b>66</b>	mV from	
	Output Voltage Swing Low	$R_L = 2 \text{ k}\Omega \text{ to V+/2}$		45	75 <b>78</b>	either rail	
		$R_L = 10 \text{ k}\Omega \text{ to V+/2}$		20	60 <b>62</b>		
I <sub>OUT</sub>	Output Current	Sourcing to V- V <sub>IN</sub> = 200 mV ( <i>Note 9</i> )	46 <b>38</b>	66			
		Sinking to V+ V <sub>IN</sub> = -200 mV ( <i>Note 9</i> )	10.5 <b>6.5</b>	23		mA	
I <sub>S</sub>	Supply Current	(per channel)		1.30	1.70 <b>2.05</b>	mA	
SR	Slew Rate	A <sub>V</sub> = +1, Rising (10% to 90%)	6.0	9.5		1////	
3n		A <sub>V</sub> = +1, Falling (90% to 10%)	7.5	11.5		V/µs	
GBW	Gain Bandwidth			17		MHz	
e	Input Referred Voltage Noise Density	f = 400 Hz		7.0		nV/√Hz	
e <sub>n</sub>		f = 1 kHz		5.8		110/1/112	
i <sub>n</sub>	Input Referred Current Noise Density	f = 1 kHz		0.01		pA/√Hz	
THD+N	Total Harmonic Distortion + Noise	$f = 1 \text{ kHz}, A_V = 1, R_L = 100 \text{ k}Ω$ $V_O = 4 V_{PP}$		0.001		%	
		$f = 1 \text{ kHz}, A_V = 1, R_L = 600\Omega$ $V_O = 4 V_{PP}$		0.004		/0	

**Note 1:** Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics Tables.

Note 2: Human Body Model, applicable std. MIL-STD-883, Method 3015.7. Machine Model, applicable std. JESD22-A115-A (ESD MM std. of JEDEC) Field-Induced Charge-Device Model, applicable std. JESD22-C101-C (ESD FICDM std. of JEDEC).

Note 3: The maximum power dissipation is a function of  $T_{J(MAX)}$ ,  $\theta_{JA}$ . The maximum allowable power dissipation at any ambient temperature is  $P_D = (T_{J(MAX)} - T_A)/\theta_{JA}$ . All numbers apply for packages soldered directly onto a PC Board.

Note 4: Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not guaranteed on shipped production material.

Note 5: Limits are 100% production tested at 25°C. Limits over the operating temperature range are guaranteed through correlations using the Statistical Quality Control (SQC) method.

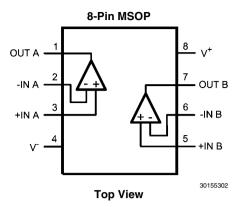
Note 6: Offset voltage average drift is determined by dividing the change in  $V_{OS}$  at the temperature extremes by the total temperature change.

Note 7: Positive current corresponds to current flowing into the device.

Note 8: This parameter is guaranteed by design and/or characterization and is not tested in production.

Note 9: The short circuit test is a momentary open loop test.

# **Connection Diagram**

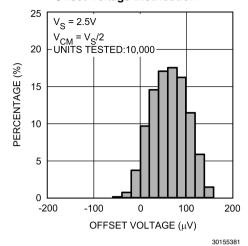


# **Ordering Information**

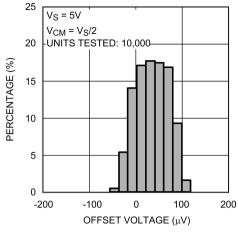
Package	Part Number	Package Marking	Transport Media	NSC Drawing	Features
	SM73307MM		1k Units Tape and Reel		
8-Pin MSOP	SM73307MME	S307	250 Units Tape and Reel	MUA08A	Renewable Energy Grade
	SM73307MMX		3.5k Units Tape and Reel		

# **Typical Performance Characteristics** Unless otherwise noted: $T_A = 25^{\circ}C$ , $V_S = 5V$ , $V_{CM} = V_S/2$ .

#### Offset Voltage Distribution

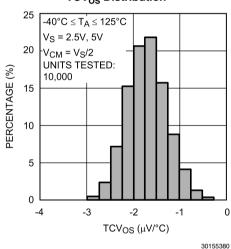


#### Offset Voltage Distribution

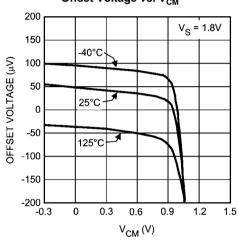


30155322

## **TCV<sub>OS</sub> Distribution**

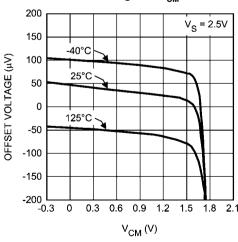


Offset Voltage vs. V<sub>CM</sub>

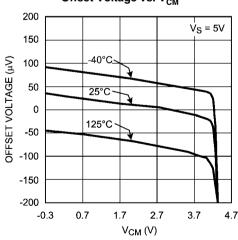


30155310

### Offset Voltage vs. V<sub>CM</sub>

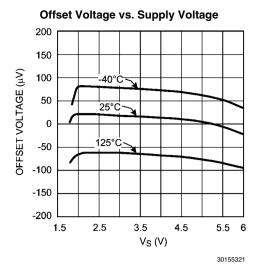


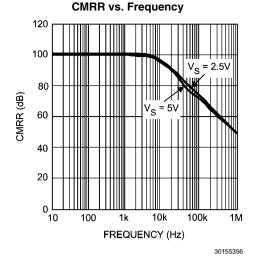
Offset Voltage vs. V<sub>CM</sub>



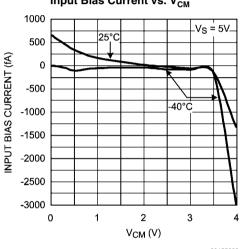
30155312

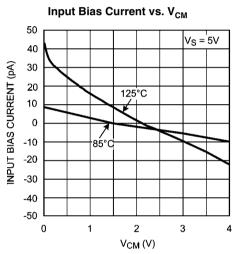
www.national.com 6



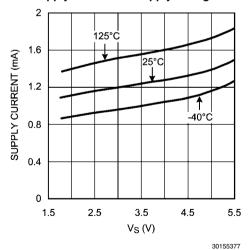


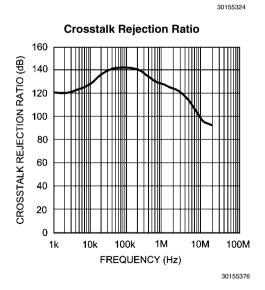
Input Bias Current vs.  $V_{\rm CM}$ 



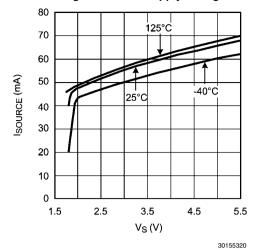


Supply Current vs. Supply Voltage

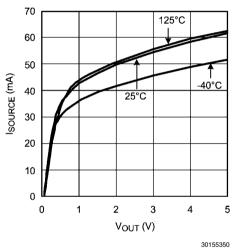




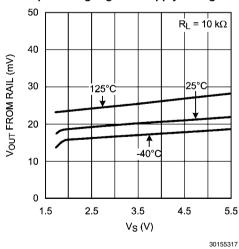
#### Sourcing Current vs. Supply Voltage



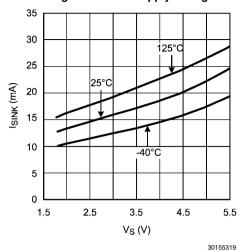
### Sourcing Current vs. Output Voltage

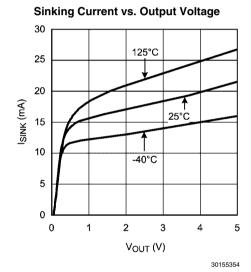


### **Output Swing High vs. Supply Voltage**

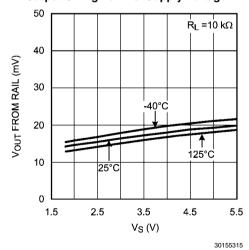


#### Sinking Current vs. Supply Voltage

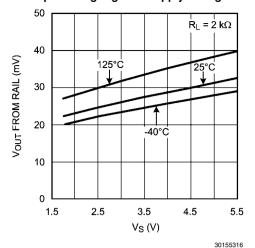




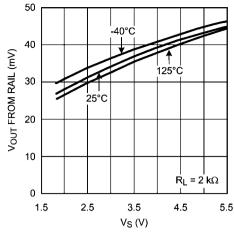
### **Output Swing Low vs. Supply Voltage**



#### **Output Swing High vs. Supply Voltage**

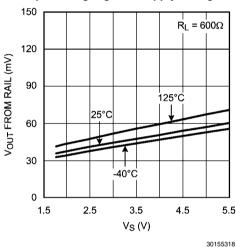


# Output Swing Low vs. Supply Voltage



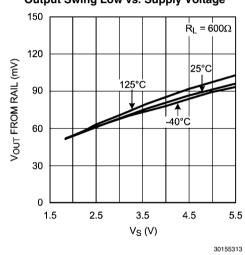
#### 30155314

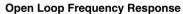
#### **Output Swing High vs. Supply Voltage**

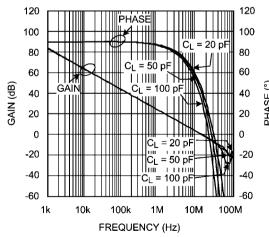


#### 30155318

## **Output Swing Low vs. Supply Voltage**



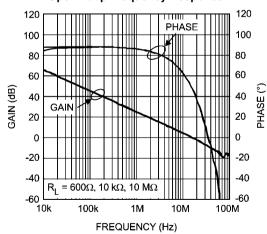


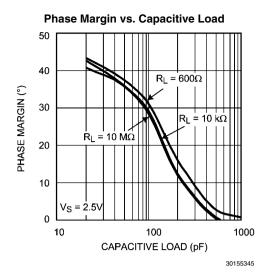


#### 30155341

9

#### **Open Loop Frequency Response**



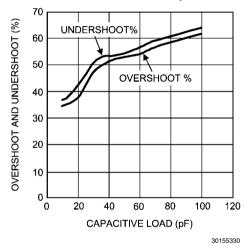


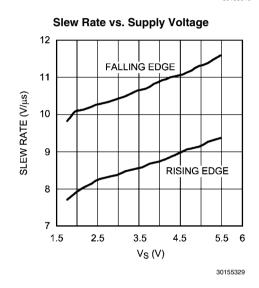
#### 

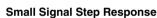
Phase Margin vs. Capacitive Load

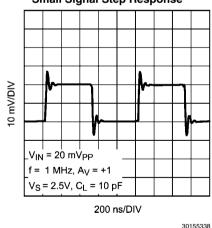
50

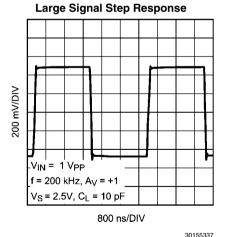
#### Overshoot and Undershoot vs. Capacitive Load



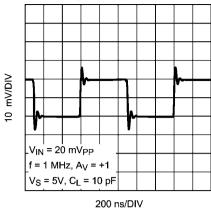




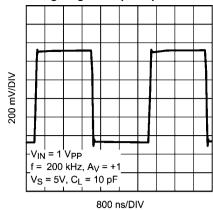




#### **Small Signal Step Response**



#### Large Signal Step Response

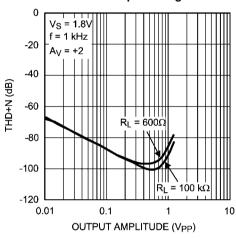


30155334

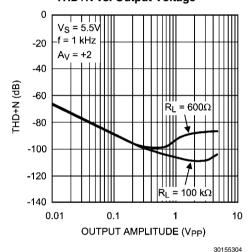
#### THD+N vs. Output Voltage

30155333

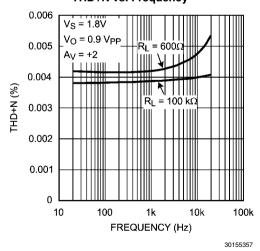
30155326



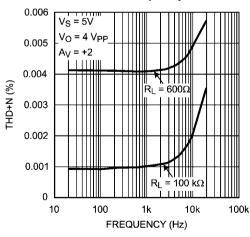
THD+N vs. Output Voltage



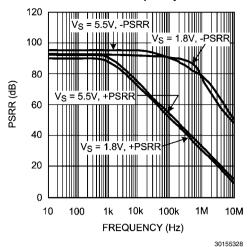
THD+N vs. Frequency



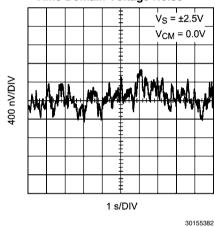
THD+N vs. Frequency



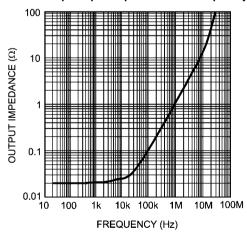
#### **PSRR vs. Frequency**



## **Time Domain Voltage Noise**

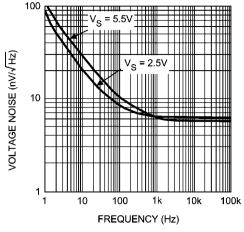


#### **Closed Loop Output Impedance vs. Frequency**



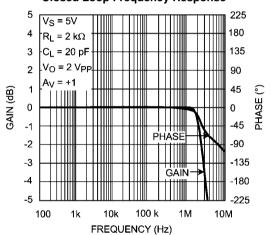
30155332

#### Input Referred Voltage Noise vs. Frequency



#### 30155339

### **Closed Loop Frequency Response**



30155336

# **Application Information**

The SM73307 is a dual, low noise, low offset, rail-to-rail output precision amplifier with a wide gain bandwidth product of 17 MHz and low supply current. The wide bandwidth makes the SM73307 an ideal choice for wide-band amplification in photovoltaic and portable applications.

The SM73307 is superior for sensor applications. The very low input referred voltage noise of only 5.8 nV/ $\sqrt{\rm Hz}$  at 1 kHz and very low input referred current noise of only 10 fA/ $\sqrt{\rm Hz}$  mean more signal fidelity and higher signal-to-noise ratio.

The SM73307 has a supply voltage range of 1.8V to 5.5V over a wide temperature range of 0°C to 125°C. This is optimal for low voltage commercial applications. For applications where the ambient temperature might be less than 0°C, the SM73307 is fully operational at supply voltages of 2.0V to 5.5V over the temperature range of -40°C to 125°C.

The outputs of the SM73307 swing within 25 mV of either rail providing maximum dynamic range in applications requiring low supply voltage. The input common mode range of the SM73307 extends to 300 mV below ground. This feature enables users to utilize this device in single supply applications.

The use of a very innovative feedback topology has enhanced the current drive capability of the SM73307, resulting in sourcing currents of as much as 47 mA with a supply voltage of only 1.8V.

The SM73307 is offered in an 8-pin MSOP package. This small package is an ideal solution for applications requiring minimum PC board footprint.

#### **CAPACITIVE LOAD**

The unity gain follower is the most sensitive configuration to capacitive loading. The combination of a capacitive load placed directly on the output of an amplifier along with the output impedance of the amplifier creates a phase lag which in turn reduces the phase margin of the amplifier. If phase margin is significantly reduced, the response will be either under-damped or the amplifier will oscillate.

The SM73307 can directly drive capacitive loads of up to 120 pF without oscillating. To drive heavier capacitive loads, an isolation resistor,  $\rm R_{\rm ISO}$  as shown in *Figure 1*, should be used. This resistor and  $\rm C_L$  form a pole and hence delay the phase lag or increase the phase margin of the overall system. The larger the value of  $\rm R_{\rm ISO}$ , the more stable the output voltage will be. However, larger values of  $\rm R_{\rm ISO}$  result in reduced output swing and reduced output current drive.

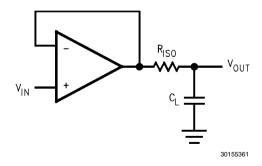


FIGURE 1. Isolating Capacitive Load

#### **INPUT CAPACITANCE**

CMOS input stages inherently have low input bias current and higher input referred voltage noise. The SM73307 enhances this performance by having the low input bias current of only 50 fA, as well as, a very low input referred voltage noise of 5.8 nV/√Hz. In order to achieve this a larger input stage has been used. This larger input stage increases the input capacitance of the SM73307. *Figure 2* shows typical input common mode capacitance of the SM73307.

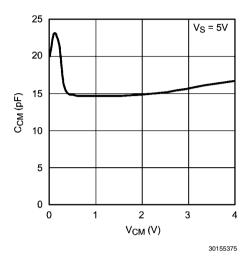


FIGURE 2. Input Common Mode Capacitance

This input capacitance will interact with other impedances, such as gain and feedback resistors which are seen on the inputs of the amplifier, to form a pole. This pole will have little or no effect on the output of the amplifier at low frequencies and under DC conditions, but will play a bigger role as the frequency increases. At higher frequencies, the presence of this pole will decrease phase margin and also cause gain peaking. In order to compensate for the input capacitance, care must be taken in choosing feedback resistors. In addition to being selective in picking values for the feedback resistor, a capacitor can be added to the feedback path to increase stability.

The DC gain of the circuit shown in Figure 3 is simply  $-R_2/R_1$ .

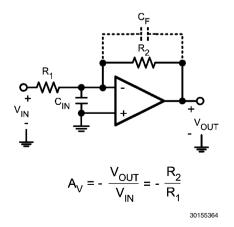


FIGURE 3. Compensating for Input Capacitance

For the time being, ignore  $C_F$ . The AC gain of the circuit in *Figure 3* can be calculated as follows:

$$\frac{V_{OUT}}{V_{IN}}(s) = \frac{-R_2/R_1}{\left[1 + \frac{s}{\left(\frac{A_0 R_1}{R_1 + R_2}\right)} + \frac{s^2}{\left(\frac{A_0}{C_{IN} R_2}\right)}\right]}$$
(1)

This equation is rearranged to find the location of the two poles:

$$P_{1,2} = \frac{-1}{2C_{IN}} \left[ \frac{1}{R_1} + \frac{1}{R_2} \pm \sqrt{\left(\frac{1}{R_1} + \frac{1}{R_2}\right)^2 - \frac{4A_0C_{IN}}{R_2}} \right]$$
(2)

As shown in *Equation 2*, as the values of  $\rm R_1$  and  $\rm R_2$  are increased, the magnitude of the poles are reduced, which in turn decreases the bandwidth of the amplifier. *Figure 4* shows the frequency response with different value resistors for  $\rm R_1$  and  $\rm R_2$ . Whenever possible, it is best to choose smaller feedback resistors.

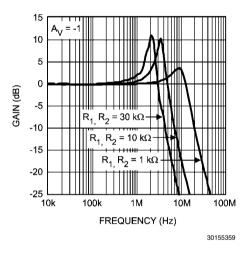


FIGURE 4. Closed Loop Frequency Response

As mentioned before, adding a capacitor to the feedback path will decrease the peaking. This is because  $C_F$  will form yet another pole in the system and will prevent pairs of poles, or complex conjugates from forming. It is the presence of pairs of poles that cause the peaking of gain. Figure 5 shows the frequency response of the schematic presented in Figure 3 with different values of  $C_F$ . As can be seen, using a small value capacitor significantly reduces or eliminates the peaking.

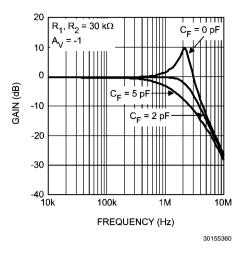


FIGURE 5. Closed Loop Frequency Response

#### TRANSIMPEDANCE AMPLIFIER

In many applications the signal of interest is a very small amount of current that needs to be detected. Current that is transmitted through a photodiode is a good example. Barcode scanners, light meters, fiber optic receivers, and industrial sensors are some typical applications utilizing photodiodes for current detection. This current needs to be amplified before it can be further processed. This amplification is performed using a current-to-voltage converter configuration or transimpedance amplifier. The signal of interest is fed to the inverting input of an op amp with a feedback resistor in the current path. The voltage at the output of this amplifier will be equal to the negative of the input current times the value of the feedback resistor. Figure 6 shows a transimpedance amplifier configuration.  $\mathbf{C}_{\mathrm{D}}$  represents the photodiode parasitic capacitance and  ${\rm C}_{\rm CM}$  denotes the common-mode capacitance of the amplifier. The presence of all of these capacitance tances at higher frequencies might lead to less stable topologies at higher frequencies. Care must be taken when designing a transimpedance amplifier to prevent the circuit from oscillating.

With a wide gain bandwidth product, low input bias current and low input voltage and current noise, the SM73307 is ideal for wideband transimpedance applications.

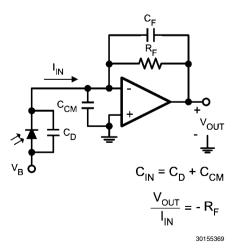


FIGURE 6. Transimpedance Amplifier

A feedback capacitance  $C_F$  is usually added in parallel with  $R_F$  to maintain circuit stability and to control the frequency response. To achieve a maximally flat,  $2^{nd}$  order response,  $R_F$  and  $C_F$  should be chosen by using *Equation 3* 

$$C_{F} = \sqrt{\frac{C_{IN}}{GBWP * 2 \pi R_{F}}}$$
(3)

Calculating  $C_F$  from *Equation 3* can sometimes result in capacitor values which are less than 2 pF. This is especially the case for high speed applications. In these instances, it is often more practical to use the circuit shown in *Figure 7* in order to allow more sensible choices for  $C_F$ . The new feedback capacitor,  $C_F'$ , is  $(1+R_B/R_A)$   $C_F$ . This relationship holds as long as  $R_A << R_F$ .

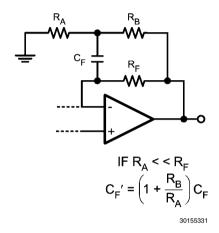


FIGURE 7. Modified Transimpedance Amplifier

#### **SENSOR INTERFACE**

The SM73307 has a low input bias current and low input referred noise, which makes it an ideal choice for sensor interfaces such as thermopiles, Infra Red (IR) thermometry, thermocouple amplifiers, and pH electrode buffers.

Thermopiles generate voltage in response to receiving radiation. These voltages are often only a few microvolts. As a result, the operational amplifier used for this application needs to have low offset voltage, low input voltage noise, and low input bias current. Figure 8 shows a thermopile application where the sensor detects radiation from a distance and generates a voltage that is proportional to the intensity of the radiation. The two resistors,  $\rm R_A$  and  $\rm R_B$ , are selected to provide high gain to amplify this signal, while  $\rm C_F$  removes the high frequency noise.

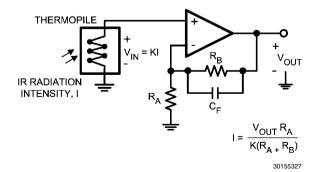


FIGURE 8. Thermopile Sensor Interface

#### **PRECISION RECTIFIER**

Rectifiers are electrical circuits used for converting AC signals to DC signals. *Figure 9* shows a full-wave precision rectifier. Each operational amplifier used in this circuit has a diode on its output. This means for the diodes to conduct, the output of the amplifier needs to be positive with respect to ground. If  $\rm V_{IN}$  is in its positive half cycle then only the output of the bottom amplifier will be positive. As a result, the diode on the output of the bottom amplifier will conduct and the signal will show at the output of the circuit. If  $\rm V_{IN}$  is in its negative half cycle then the output of the top amplifier will be positive, resulting in the diode on the output of the top amplifier conducting and delivering the signal from the amplifier's output to the circuit's output.

For  $R_2/R_1 \ge 2$ , the resistor values can be found by using the equation shown in *Figure 9*. If  $R_2/R_1 = 1$ , then  $R_3$  should be left open, no resistor needed, and  $R_4$  should simply be shorted.

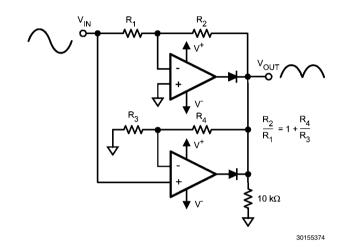
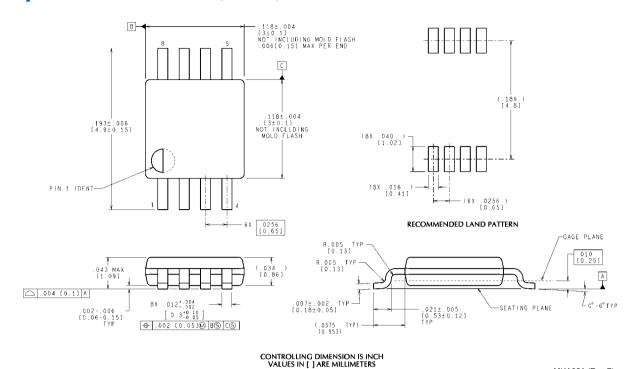


FIGURE 9. Precision Rectifier

# Physical Dimensions inches (millimeters) unless otherwise noted



8-Pin MSOP NS Package Number MUA08A

MUA08A (Rev F)

## **Notes**

For more National Semiconductor product information and proven design tools, visit the following Web sites at: www.national.com

Pr	oducts	Design Support			
Amplifiers	www.national.com/amplifiers	WEBENCH® Tools	www.national.com/webench		
Audio	www.national.com/audio	App Notes	www.national.com/appnotes		
Clock and Timing	www.national.com/timing	Reference Designs	www.national.com/refdesigns		
Data Converters	www.national.com/adc	Samples	www.national.com/samples		
Interface	www.national.com/interface	Eval Boards	www.national.com/evalboards		
LVDS	www.national.com/lvds	Packaging	www.national.com/packaging		
Power Management	www.national.com/power	Green Compliance	www.national.com/quality/green		
Switching Regulators	www.national.com/switchers	Distributors	www.national.com/contacts		
LDOs	www.national.com/ldo	Quality and Reliability	www.national.com/quality		
LED Lighting	www.national.com/led	Feedback/Support	www.national.com/feedback		
Voltage References	www.national.com/vref	Design Made Easy	www.national.com/easy		
PowerWise® Solutions	www.national.com/powerwise	Applications & Markets	www.national.com/solutions		
Serial Digital Interface (SDI)	www.national.com/sdi	Mil/Aero	www.national.com/milaero		
Temperature Sensors	www.national.com/tempsensors	SolarMagic™	www.national.com/solarmagic		
PLL/VCO	www.national.com/wireless	PowerWise® Design University	www.national.com/training		

THE CONTENTS OF THIS DOCUMENT ARE PROVIDED IN CONNECTION WITH NATIONAL SEMICONDUCTOR CORPORATION ("NATIONAL") PRODUCTS. NATIONAL MAKES NO REPRESENTATIONS OR WARRANTIES WITH RESPECT TO THE ACCURACY OR COMPLETENESS OF THE CONTENTS OF THIS PUBLICATION AND RESERVES THE RIGHT TO MAKE CHANGES TO SPECIFICATIONS AND PRODUCT DESCRIPTIONS AT ANY TIME WITHOUT NOTICE. NO LICENSE, WHETHER EXPRESS, IMPLIED, ARISING BY ESTOPPEL OR OTHERWISE, TO ANY INTELLECTUAL PROPERTY RIGHTS IS GRANTED BY THIS DOCUMENT.

TESTING AND OTHER QUALITY CONTROLS ARE USED TO THE EXTENT NATIONAL DEEMS NECESSARY TO SUPPORT NATIONAL'S PRODUCT WARRANTY. EXCEPT WHERE MANDATED BY GOVERNMENT REQUIREMENTS, TESTING OF ALL PARAMETERS OF EACH PRODUCT IS NOT NECESSARILY PERFORMED. NATIONAL ASSUMES NO LIABILITY FOR APPLICATIONS ASSISTANCE OR BUYER PRODUCT DESIGN. BUYERS ARE RESPONSIBLE FOR THEIR PRODUCTS AND APPLICATIONS USING NATIONAL COMPONENTS. PRIOR TO USING OR DISTRIBUTING ANY PRODUCTS THAT INCLUDE NATIONAL COMPONENTS, BUYERS SHOULD PROVIDE ADEQUATE DESIGN, TESTING AND OPERATING SAFEGUARDS.

EXCEPT AS PROVIDED IN NATIONAL'S TERMS AND CONDITIONS OF SALE FOR SUCH PRODUCTS, NATIONAL ASSUMES NO LIABILITY WHATSOEVER, AND NATIONAL DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY RELATING TO THE SALE AND/OR USE OF NATIONAL PRODUCTS INCLUDING LIABILITY OR WARRANTIES RELATING TO FITNESS FOR A PARTICULAR PURPOSE, MERCHANTABILITY, OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

#### LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS PRIOR WRITTEN APPROVAL OF THE CHIEF EXECUTIVE OFFICER AND GENERAL COUNSEL OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

Life support devices or systems are devices which (a) are intended for surgical implant into the body, or (b) support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in a significant injury to the user. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system or to affect its safety or effectiveness.

National Semiconductor and the National Semiconductor logo are registered trademarks of National Semiconductor Corporation. All other brand or product names may be trademarks or registered trademarks of their respective holders.

Copyright© 2011 National Semiconductor Corporation

For the most current product information visit us at www.national.com



National Semiconductor Americas Technical Support Center Email: support@nsc.com Tel: 1-800-272-9959 National Semiconductor Europe Technical Support Center Email: europe.support@nsc.com National Semiconductor Asia Pacific Technical Support Center Email: ap.support@nsc.com

National Semiconductor Japan Technical Support Center Email: jpn.feedback@nsc.com